Metal atomic layer deposition system

Deposition Process Library

- Titanium nitride (TiN)

Thickness

- 20 Å ~ 100 Å

Process parameters

- Process: TiN
- Precursor: $TiCl_4$
- Oxidant: H_2O (Thermal mode)
- Pressure(torr): 0.1 ~ 0.3
- Carrier gas: Ar
- Purge gas: Ar
- Temperature (℃): 400 ℃
- Substrate size: 6 or 8 inch metal-free silicon wafers, or chips